

STTH100W06C

Turbo 2 ultrafast high voltage rectifier

Datasheet - production data

Features

- Ultrafast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses
- ECOPACK®2 compliant component
- Ribbon bonding for more robustness

Description

The STTH100W06CW, uses ST Turbo 2, 600 V technology. It is especially suited to be used for DC/DC and DC/AC converters in secondary stage of MIG/MMA/TIG welding machine. Housed in ST's TO-247, this device offers high power integration for all welding machines and industrial applications.

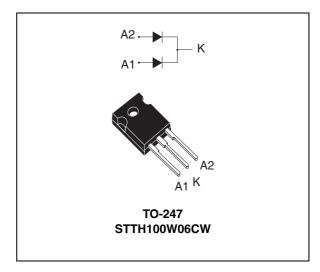


Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 50 A
V_{RRM}	600 V
t _{rr} (typ)	55 ns
T _j (max)	175 °C
V _F (typ)	0.92 V

Characteristics STTH100W06C

1 Characteristics

Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified, per diode)

Symbol	Paramete	Value	Unit			
V_{RRM}	Repetitive peak reverse voltage			600	V	
I _{F(RMS)}	Forward rms current	Forward rms current			Α	
1	Average forward current, $\delta = 0.5$	T _c = 135 °C	Per diode	50	Α	
$I_{F(AV)}$ Average forward current, $\delta = 0.5$	T _c = 120°C	Per device	100	^		
I _{FSM}	Surge non repetitive forward current	rge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			Α	
T _{stg}	Storage temperature range	-65 to + 175	°C			
T _j	Maximum operating junction tempera	+ 175	°C			

Table 3. Thermal resistance

Symbol	Parameter		Value	Unit
В	Junction to case	Per diode	0.55	°C/W
$R_{th(j-c)}$ Ju	Junction to case	Total	0.35	C / W
R _{th(c)}	Coupling		0.15	°C / W

When diodes 1 and 2 are used simultaneously:

 $T_{j}(diode 1) = P(diode 1) \times R_{th(j-c)}(per diode) + P(diode 2) \times R_{th(c)}$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾ Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}			20	μΑ	
	T _j = 125 °C			20	200		
	V (2) Famural valtage dues	T _j = 25 °C	I _F = 50A			1.45	
V _F ⁽²⁾		T _j = 150 °C			0.92	1.15	v
V _F ⁽²⁾ Forward voltage drop	T _j = 25 °C	1 100 4			1.65	\ \ \	
		T _j = 150 °C	I _F = 100 A		1.15	1.45	

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.85 \text{ x } I_{F(AV)} + 0.006 I_{F}^{2}_{(RMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

STTH100W06C Characteristics

 Table 5.
 Dynamic electrical characteristics (per diode)

Symbol	Parameter	Test conditions			Тур.	Max.	Unit
I _{RM}	Reverse recovery current		50.4.1/ 400.1/		30	40	Α
Q _{RR}	Reverse recovery charge	T _j = 125 °C	$I_F = 50 \text{ A}, V_R = 400 \text{ V}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$		3700		nC
S _{factor}	Softness factor				0.3		
t _{rr}	Reverse recovery time	T _j = 25 °C	$I_F = 1 \text{ A}, V_R = 30 \text{ V}$ $dI_F/dt = -100 \text{ A/}\mu\text{s}$		55	75	ns
t _{fr}	Forward recovery time	$T_j = 25 ^{\circ}\text{C}$ $I_F = 50 \text{A}, V_{FR} = 1.0 \text{V}$				200	ns
V _{FP}	Forward recovery voltage	T _j = 25 °C	dI _F /dt = 200 A/μs		1.3	2	٧

Figure 1. Average forward power dissipation Figure 2. Forward voltage drop versus versus average forward current (per diode) forward current (per diode)

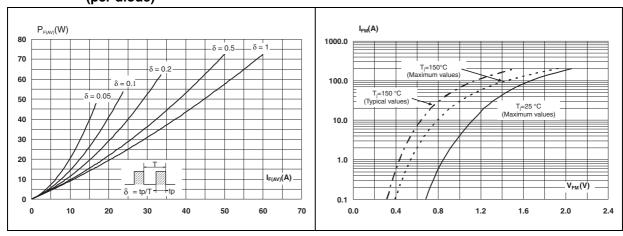


Figure 4.

Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Peak reverse recovery current

versus dl_F/dt (typical values, per

Zth(j-c)/Rth(j-c)

1.0

0.9

0.8

0.7

0.6

0.5

0.4

0.3

0.2

Single pulse

0.1

1.E-04

1.E-03

1.E-02

1.E-01

1.E+00

Characteristics STTH100W06C

Figure 5. Reverse recovery time versus dl_F/dt Figure 6. Reverse recovery charges versus dl_F/dt (typical values, per diode)

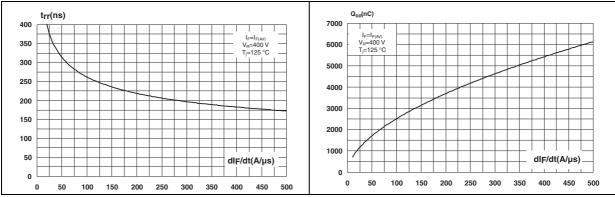


Figure 7. Reverse recovery softness factor versus dl_F/dt (typical values, per diode)

Figure 8. Relative variation of dynamic parameters versus junction temperature

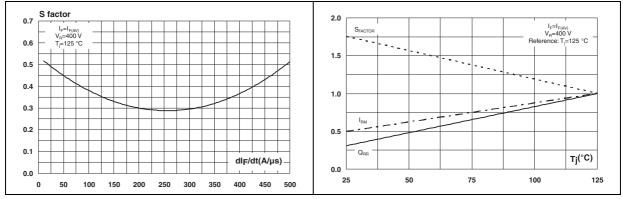
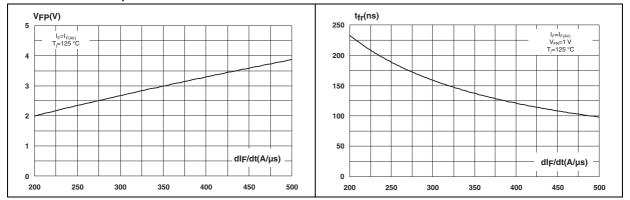


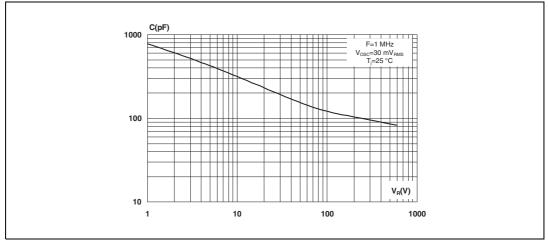
Figure 9. Transient peak forward voltage versus dl_F/dt (typical values, per diode)

Figure 10. Forward recovery time versus dI_F/dt (typical values, per diode)



STTH100W06C Characteristics

Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



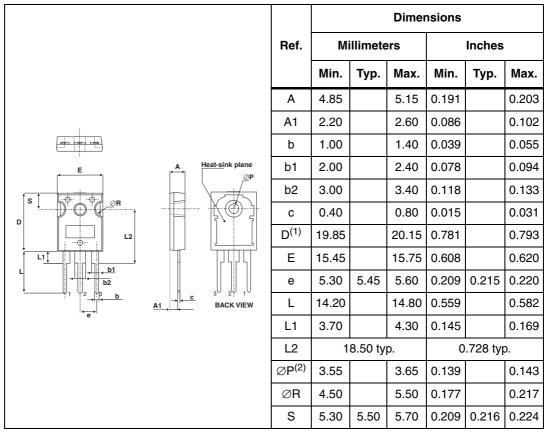
Package information STTH100W06C

2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m (1.0 N·m maximum)

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Table 6. TO-247 dimensions



- 1. Dimension D plus gate protrusion does not exceed 20.5 mm
- 2. Resin thickness around the mounting hole is not less than 0.9 mm

3 Ordering information

Table 7. Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH100W06CW	STTH100W06CW	TO-247	4.46 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
05-Oct-2012	1	First issue.

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4

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